

## Phase Control Thyristors (Hockey PUK Version), 410 A



A-PUK (TO-200AB)

### FEATURES

- Center amplifying gate
- Metal case with ceramic insulator
- International standard case A-PUK (TO-200AB)
- Designed and qualified for industrial level

### TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

PRIMARY CHARACTERISTICS	
$I_{T(AV)}$	410 A
$V_{DRM}/V_{RRM}$	400 V, 800 V, 1200 V, 1400 V, 1600 V, 1800 V, 2000 V
$V_{TM}$	1.69 V
$I_{GT}$	90 mA
$T_J$	-40 °C to +125 °C
Package	A-PUK (TO-200AB)
Circuit configuration	Single SCR

MAJOR RATINGS AND CHARACTERISTICS			
PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{T(AV)}$		410	A
	$T_{hs}$	55	°C
$I_{T(RMS)}$		780	A
	$T_{hs}$	25	°C
$I_{TSM}$	50 Hz	5700	A
	60 Hz	5970	
$I^2t$	50 Hz	163	kA <sup>2</sup> s
	60 Hz	149	
$V_{DRM}/V_{RRM}$		400 to 2000	V
$t_q$	Typical	100	μs
$T_J$		-40 to +125	°C

### ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS				
TYPE NUMBER	VOLTAGE CODE	$V_{DRM}/V_{RRM}$ , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	$V_{RSM}$ , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	$I_{DRM}/I_{RRM}$ , MAXIMUM AT $T_J = T_J$ MAXIMUM mA
VS-ST230C..C	04	400	500	30
	08	800	900	
	12	1200	1300	
	14	1400	1500	
	16	1600	1700	
	18	1800	1900	
	20	2000	2100	

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum average on-state current at heatsink temperature	$I_{T(AV)}$	180° conduction, half sine wave double side (single side) cooled		410 (165)	A
				55 (85)	°C
Maximum RMS on-state current	$I_{T(RMS)}$	DC at 25 °C heatsink temperature double side cooled		780	
Maximum peak, one-cycle non-repetitive surge current	$I_{TSM}$	t = 10 ms	No voltage reapplied	5700	A
		t = 8.3 ms			
		t = 10 ms	100 % $V_{RRM}$ reapplied	4800	
		t = 8.3 ms		5000	
Maximum $I^2t$ for fusing	$I^2t$	t = 10 ms	No voltage reapplied	163	kA <sup>2</sup> s
		t = 8.3 ms			
		t = 10 ms	100 % $V_{RRM}$ reapplied	115	
		t = 8.3 ms		105	
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	t = 0.1 to 10 ms, no voltage reapplied		1630	kA <sup>2</sup> √s
Low level value of threshold voltage	$V_{T(TO)1}$	(16.7 % $\times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)}$ ), $T_J = T_J$ maximum		0.92	V
High level value of threshold voltage	$V_{T(TO)2}$	(I > $\pi \times I_{T(AV)}$ ), $T_J = T_J$ maximum		0.98	
Low level value of on-state slope resistance	$r_{t1}$	(16.7 % $\times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)}$ ), $T_J = T_J$ maximum		0.88	mΩ
High level value of on-state slope resistance	$r_{t2}$	(I > $\pi \times I_{T(AV)}$ ), $T_J = T_J$ maximum		0.81	
Maximum on-state voltage	$V_{TM}$	$I_{pk} = 880$ A, $T_J = T_J$ maximum, $t_p = 10$ ms sine pulse		1.69	V
Maximum holding current	$I_H$	$T_J = 25$ °C, anode supply 12 V resistive load		600	mA
Maximum (typical) latching current	$I_L$			1000 (300)	

SWITCHING					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum non-repetitive rate of rise of turned-on current	$di/dt$	Gate drive 20 V, 20 Ω, $t_r \leq 1$ μs $T_J = T_J$ maximum, anode voltage $\leq 80$ % $V_{DRM}$		1000	A/μs
Typical delay time	$t_d$	Gate current 1 A, $di_g/dt = 1$ A/μs $V_d = 0.67$ % $V_{DRM}$ , $T_J = 25$ °C		1.0	μs
Typical turn-off time	$t_q$	$I_{TM} = 300$ A, $T_J = T_J$ maximum, $di/dt = 20$ A/μs, $V_R = 50$ V, $dV/dt = 20$ V/μs, gate 0 V 100 Ω, $t_p = 500$ μs		100	

BLOCKING					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum critical rate of rise of off-state voltage	$dV/dt$	$T_J = T_J$ maximum linear to 80 % rated $V_{DRM}$		500	V/μs
Maximum peak reverse and off-state leakage current	$I_{RRM}$ , $I_{DRM}$	$T_J = T_J$ maximum, rated $V_{DRM}/V_{RRM}$ applied		30	mA

TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES		UNITS
			TYP.	MAX.	
Maximum peak gate power	$P_{GM}$	$T_J = T_J$ maximum, $t_p \leq 5$ ms	10.0		W
Maximum average gate power	$P_{G(AV)}$	$T_J = T_J$ maximum, $f = 50$ Hz, $d\% = 50$	2.0		
Maximum peak positive gate current	$I_{GM}$	$T_J = T_J$ maximum, $t_p \leq 5$ ms	3.0		A
Maximum peak positive gate voltage	$+V_{GM}$	$T_J = T_J$ maximum, $t_p \leq 5$ ms	20		V
Maximum peak negative gate voltage	$-V_{GM}$		5.0		
DC gate current required to trigger	$I_{GT}$	$T_J = -40$ °C	180	-	mA
		$T_J = 25$ °C	90	150	
		$T_J = 125$ °C	40	-	
DC gate voltage required to trigger	$V_{GT}$	$T_J = -40$ °C	2.9	-	V
		$T_J = 25$ °C	1.8	3.0	
		$T_J = 125$ °C	1.2	-	
DC gate current not to trigger	$I_{GD}$	$T_J = T_J$ maximum	10		mA
DC gate voltage not to trigger	$V_{GD}$		0.25		V

THERMAL AND MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum operating temperature range	$T_J$		-40 to 125	°C
Maximum storage temperature range	$T_{Stg}$		-40 to 150	
Maximum thermal resistance, junction to heatsink	$R_{thJ-hs}$	DC operation single side cooled	0.17	K/W
		DC operation double side cooled	0.08	
Maximum thermal resistance, case to heatsink	$R_{thC-hs}$	DC operation single side cooled	0.033	
		DC operation double side cooled	0.017	
Mounting force, $\pm 10$ %			4900 (500)	N (kg)
Approximate weight			50	g
Case style		See dimensions - link at the end of datasheet	A-PUK (TO-200AB)	

$\Delta R_{thJC}$ CONDUCTION						
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION		RECTANGULAR CONDUCTION		TEST CONDITIONS	UNITS
	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE		
180°	0.015	0.017	0.011	0.011	$T_J = T_J$ maximum	K/W
120°	0.018	0.019	0.019	0.019		
90°	0.024	0.024	0.026	0.026		
60°	0.035	0.035	0.036	0.036		
30°	0.060	0.060	0.060	0.061		

**Note**

- The table above shows the increment of thermal resistance  $R_{thJC}$  when devices operate at different conduction angles than DC

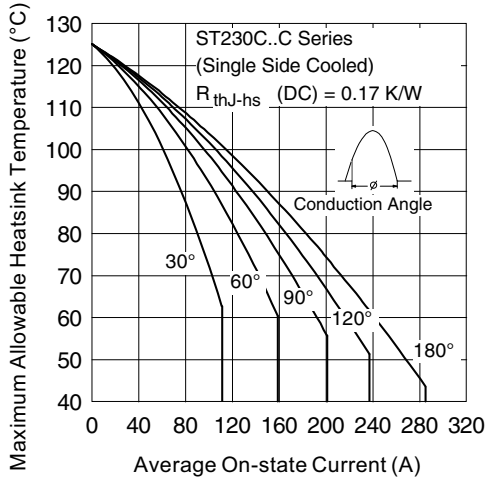


Fig. 1 - Current Ratings Characteristics

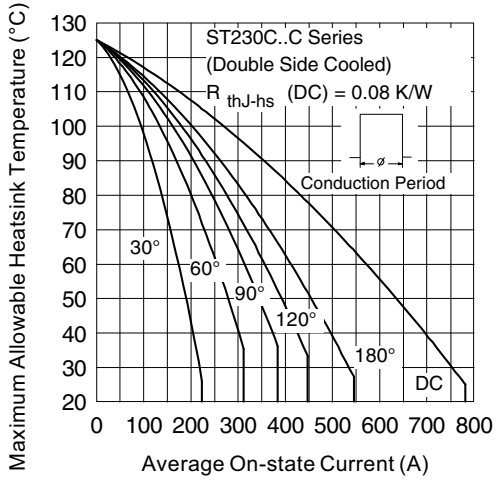


Fig. 4 - Current Ratings Characteristics

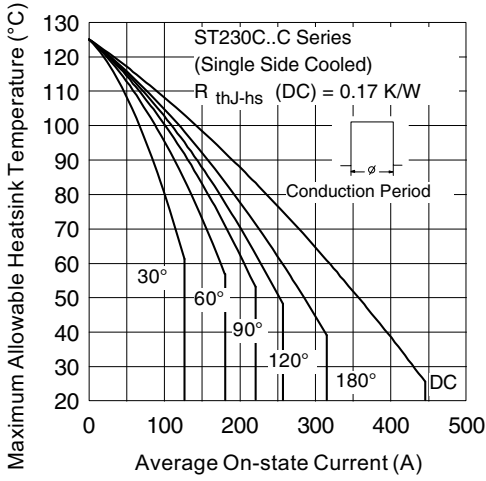


Fig. 2 - Current Ratings Characteristics

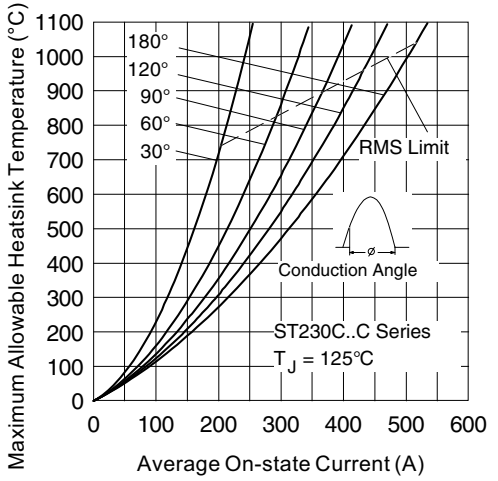


Fig. 5 - On-State Power Loss Characteristics

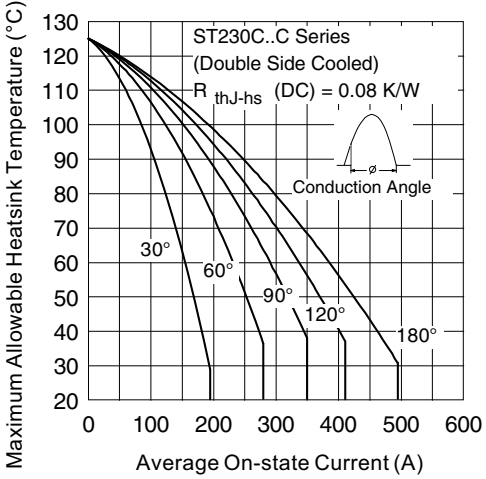


Fig. 3 - Current Ratings Characteristics

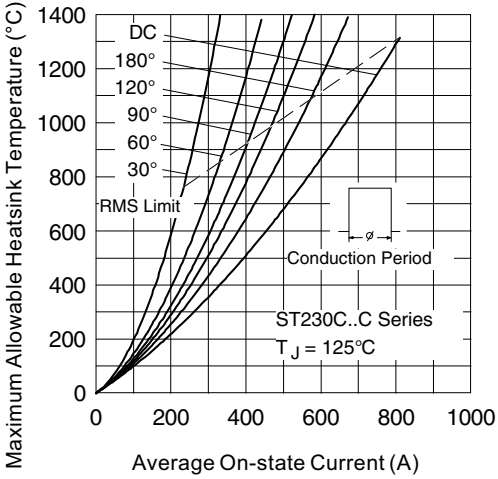


Fig. 6 - On-State Power Loss Characteristics

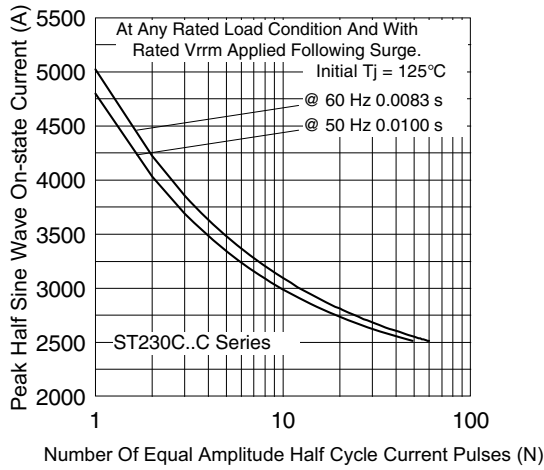


Fig. 7 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

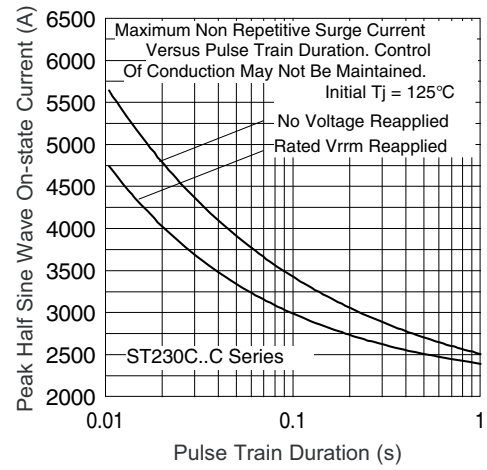


Fig. 8 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

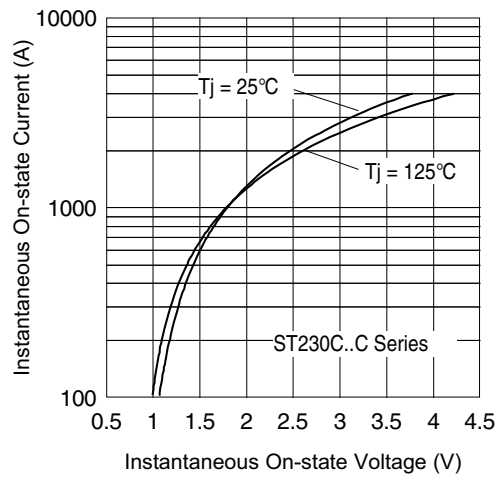


Fig. 9 - On-State Voltage Drop Characteristics

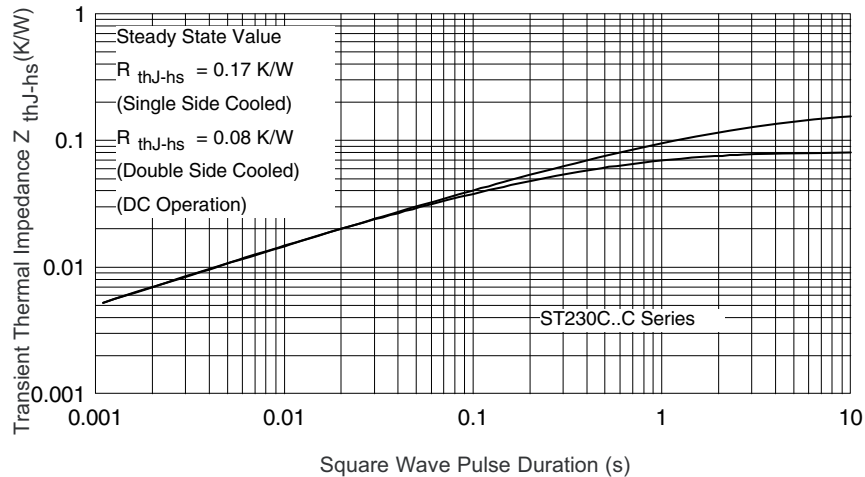


Fig. 10 - Thermal Impedance  $Z_{thJ-hs}$  Characteristics

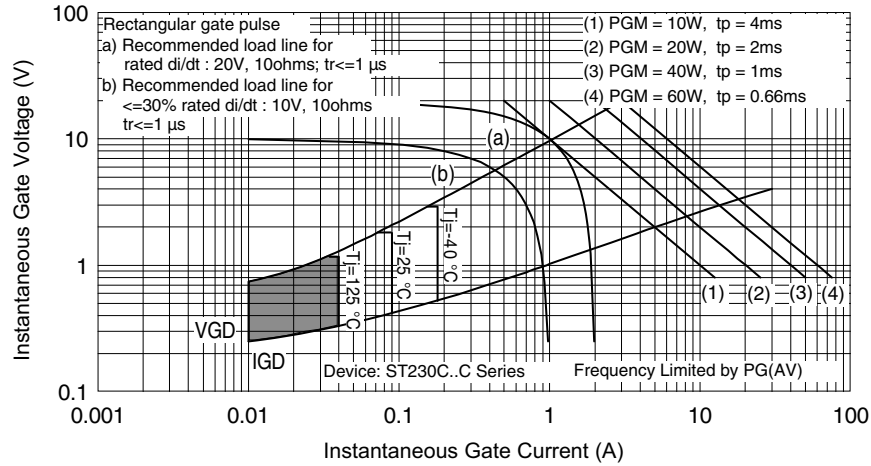


Fig. 11 - Gate Characteristics

## ORDERING INFORMATION TABLE

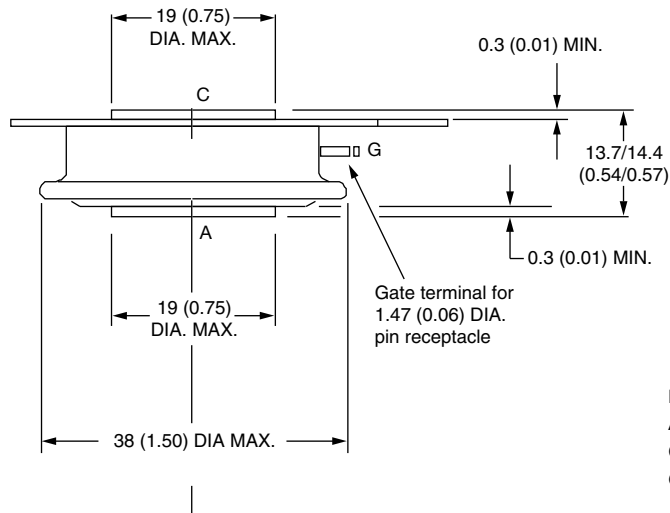
Device code	<b>VS-</b>	<b>ST</b>	<b>23</b>	<b>0</b>	<b>C</b>	<b>20</b>	<b>C</b>	<b>1</b>	<b>-</b>
	(1)	(2)	(3)	(4)	(5)	(6)	(7)	(8)	(9)

- 1** - Vishay Semiconductors product
- 2** - Thyristor
- 3** - Essential part number
- 4** - 0 = converter grade
- 5** - C = ceramic PUK
- 6** - Voltage code x 100 =  $V_{RRM}$  (see Voltage Ratings table)
- 7** - C = PUK case A-PUK (TO-200AB)
- 8** - 0 = eyelet terminals (gate and auxiliary cathode unsoldered leads)  
 1 = fast-on terminals (gate and auxiliary cathode unsoldered leads)  
 2 = eyelet terminals (gate and auxiliary cathode soldered leads)  
 3 = fast-on terminals (gate and auxiliary cathode soldered leads)
- 9** - Critical dV/dt: • None = 500 V/μs (standard selection)  
 • L = 1000 V/μs (special selection)

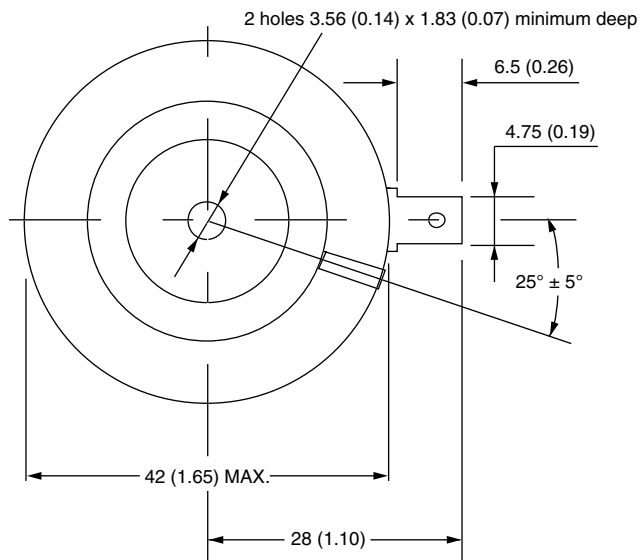
## A-PUK (TO-200AB)

**DIMENSIONS** in millimeters (inches)

Anode to gate  
Creepage distance: 7.62 (0.30) minimum  
Strike distance: 7.12 (0.28) minimum



**Note:**  
A = Anode  
C = Cathode  
G = Gate



Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)